

Silicon N Channel MOS Type (U-MOSⅢ)/Silicon Epitaxial Schottky Barrier Diode

SSM5H08TU

DC-DC Converter

- Nch MOSFET and schottky diode combined in one package
- Low RDS (ON) and low VF

Absolute Maximum Ratings (Ta = 25°C) MOSFET

| Characteristics | Symbol | Rating | Unit |
|-------------------------|-------------------------|--------------------------|------|
| Drain-Source voltage | V _{DS} | 20 | V |
| Gate-Source voltage | V _{GSS} | ±12 | V |
| Drain current | DC | I _D | 1.5 |
| | Pulse | I _{DP} (Note 2) | 6.0 |
| Drain power dissipation | P _D (Note 1) | | 0.5 |
| | | t = 10s | 0.8 |
| Channel temperature | T _{ch} | 150 | °C |

Absolute Maximum Ratings (Ta = 25°C) SCHOTTKY DIODE

| Characteristics | Symbol | Rating | Unit |
|---|------------------|-----------|------|
| Maximum (peak) reverse voltage | V _{RM} | 25 | V |
| Reverse voltage | V _R | 20 | V |
| Average forward current | I _O | 0.5 | A |
| Peak one cycle surge forward current (non-repetitive) | I _{FSM} | 2 (50 Hz) | A |
| Junction temperature | T _j | 125 | °C |

Absolute Maximum Ratings (Ta = 25°C) MOSFET, DIODE COMMON

| Characteristics | Symbol | Rating | Unit |
|-----------------------|---------------------------|---------|------|
| Storage temperature | T _{stg} | -55~125 | °C |
| Operating temperature | T _{opr} (Note 3) | -40~100 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

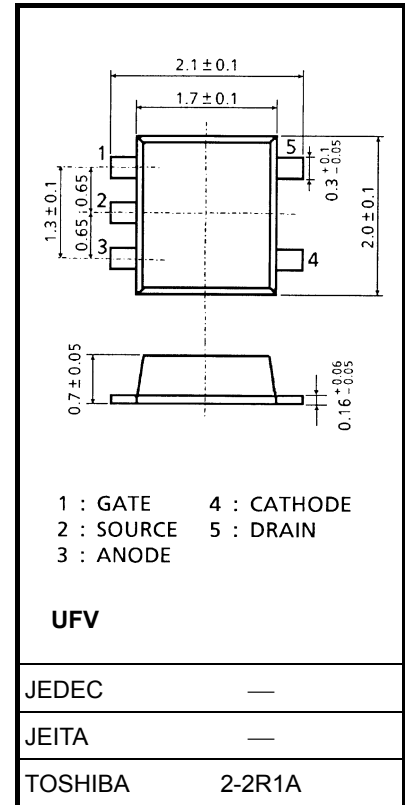
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board
(25.4 mm × 25.4 mm × 1.6 t, Cu pad: 645 mm²)

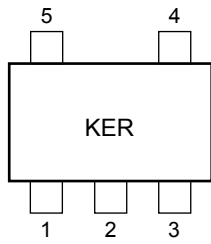
Note 2: Pulse width limited by max channel temperature

Note 3: Operating temperature limited by max channel temperature and max junction temperature

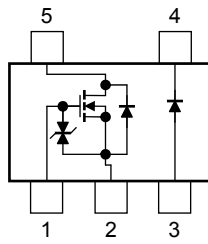
Unit: mm



Marking



Equivalent Circuit



Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

The Channel-to-Ambient thermal resistance $R_{th(ch-a)}$ and the drain power dissipation P_D vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

MOSFET

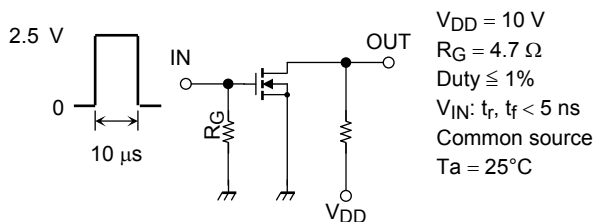
Electrical Characteristics (Ta = 25°C)

| Characteristic | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------|---------------|---------------|---|-----|------|---------|---------------|
| Gate leakage current | | I_{GSS} | $V_{GS} = \pm 12\text{ V}, V_{DS} = 0$ | — | — | ± 1 | μA |
| Drain-Source breakdown voltage | | $V_{(BR)DSS}$ | $I_D = 1\text{ mA}, V_{GS} = 0$ | 20 | — | — | V |
| | | $V_{(BR)DSX}$ | $I_D = 1\text{ mA}, V_{GS} = -12\text{ V}$ | 12 | — | — | |
| Drain Cut-off current | | I_{DSS} | $V_{DS} = 20\text{ V}, V_{GS} = 0$ | — | — | 1 | μA |
| Gate threshold voltage | | V_{th} | $V_{DS} = 3\text{ V}, I_D = 0.1\text{ mA}$ | 0.4 | — | 1.1 | V |
| Forward transfer admittance | | $ Y_{fs} $ | $V_{DS} = 3\text{ V}, I_D = 0.75\text{ A}$ (Note 4) | 1.4 | 2.8 | — | S |
| Drain-Source on-resistance | | $R_{DS(ON)}$ | $I_D = 0.75\text{ A}, V_{GS} = 4\text{ V}$ (Note 4) | — | 140 | 160 | m Ω |
| | | | $I_D = 0.75\text{ A}, V_{GS} = 2.5\text{ V}$ (Note 4) | — | 180 | 220 | |
| Input capacitance | | C_{iss} | $V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$ | — | 125 | — | pF |
| Reverse transfer capacitance | | C_{rss} | $V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$ | — | 17 | — | pF |
| Output capacitance | | C_{oss} | $V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$ | — | 42 | — | pF |
| Switching time | Turn-on time | t_{on} | $V_{DD} = 10\text{ V}, I_D = 0.75\text{ A}$ | — | 15.5 | — | ns |
| | Turn-off time | t_{off} | $V_{GS} = 0 \sim 2.5\text{ V}, R_G = 4.7\ \Omega$ | — | 8.5 | — | |

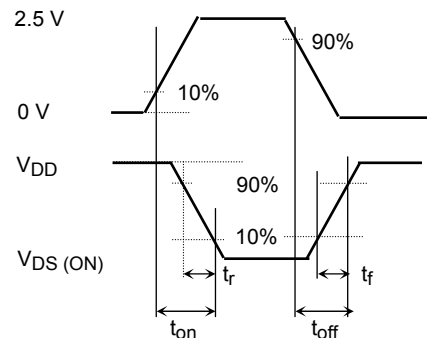
Note 4: Pulse measurement

Switching Time Test Circuit

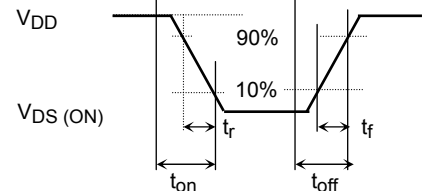
(a) Test circuit



(b) V_{IN}



(c) V_{OUT}



Precaution

V_{th} can be expressed as voltage between gate and source when the low operating current value is $I_D = 100\ \mu\text{A}$ for this product. For normal switching operation, $V_{GS(on)}$ requires a higher voltage than V_{th} and $V_{GS(off)}$ requires a lower voltage than V_{th} .

(The relationship can be established as follows: $V_{GS(off)} < V_{th} < V_{GS(on)}$)

Be sure to take this into consideration when using the device.

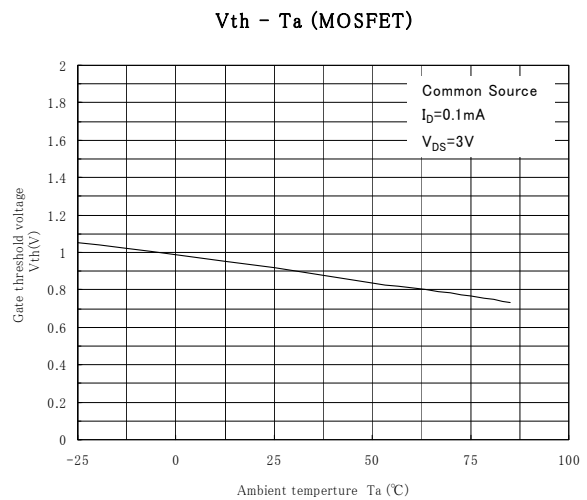
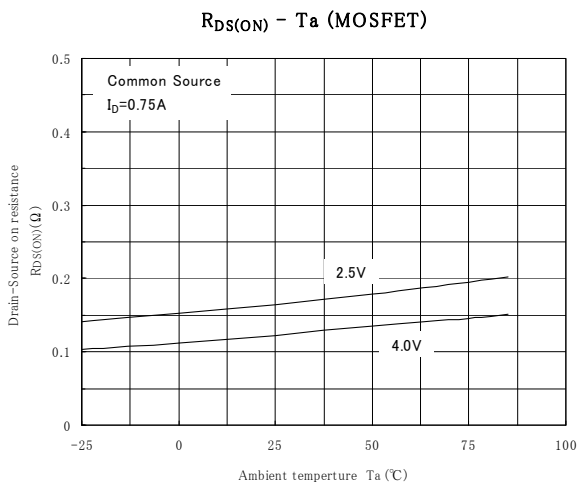
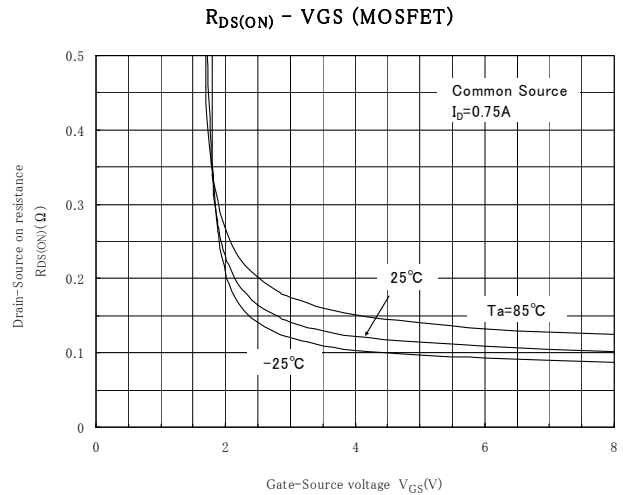
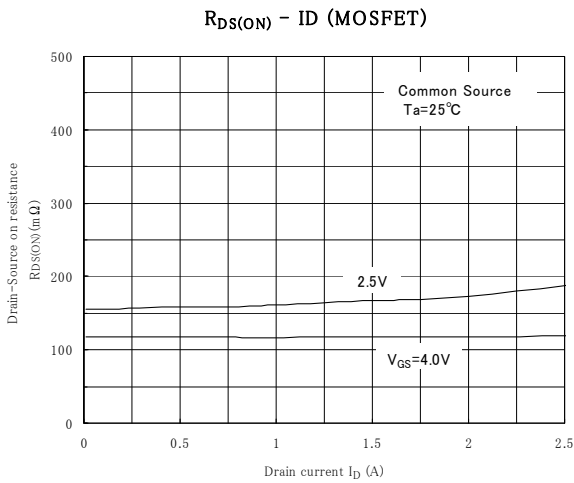
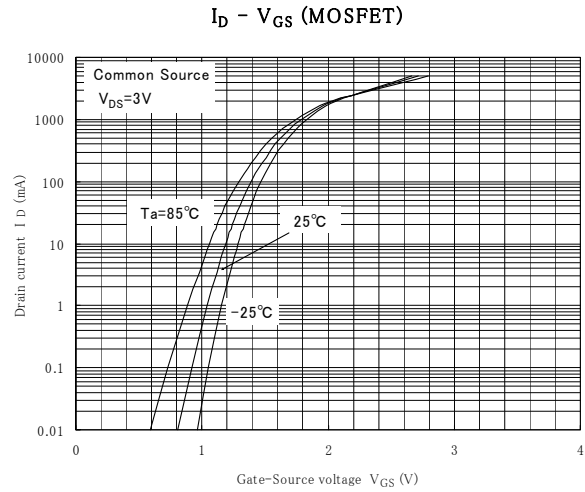
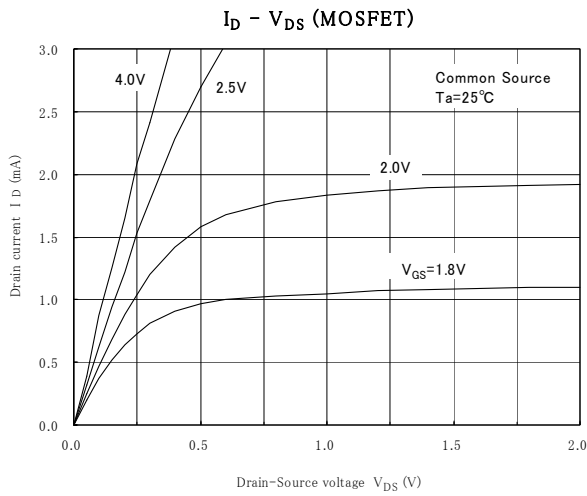
Schottky Diode**Electrical Characteristics (Ta = 25°C)**

| Characteristic | Symbol | Test Condition | Min | Typ. | Max | Unit |
|-------------------|-----------|--|-----|------|------|---------------|
| Forward voltage | $V_F (1)$ | $I_F = 0.3 \text{ A}$ | — | 0.38 | 0.45 | V |
| | $V_F (2)$ | $I_F = 0.5 \text{ A}$ | — | 0.43 | — | V |
| Reverse current | I_R | $V_R = 20 \text{ V}$ | — | — | 50 | μA |
| Total capacitance | C_T | $V_R = 0 \text{ V}, f = 1 \text{ MHz}$ | — | 46 | — | pF |

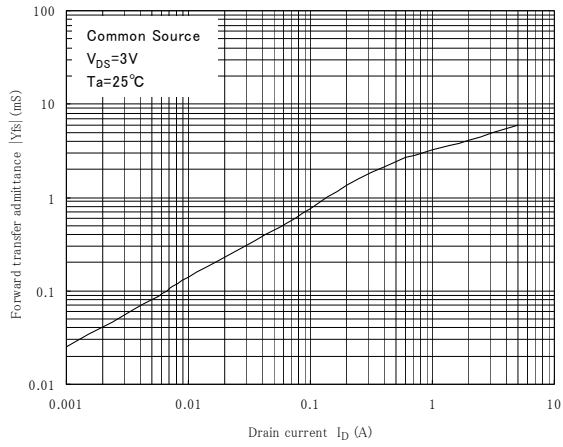
Precaution

The schottky barrier diodes of this product have large-reverse-current-leakage characteristics compared to other switching diodes. This current leakage and improper operating temperature or voltage may cause thermal runaway resulting in breakdown. Take forward and reverse loss into consideration in radiation design and safety design.

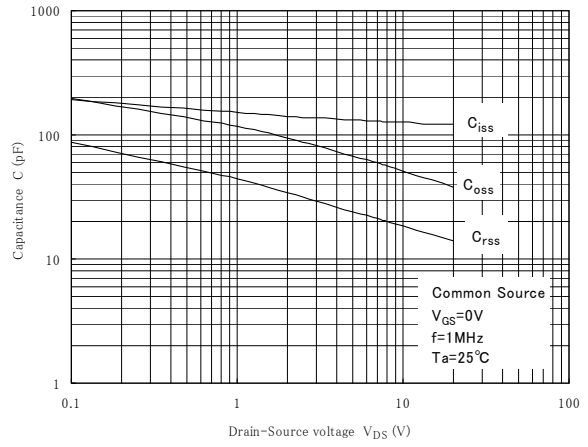
MOS Electrical Characteristics Graph



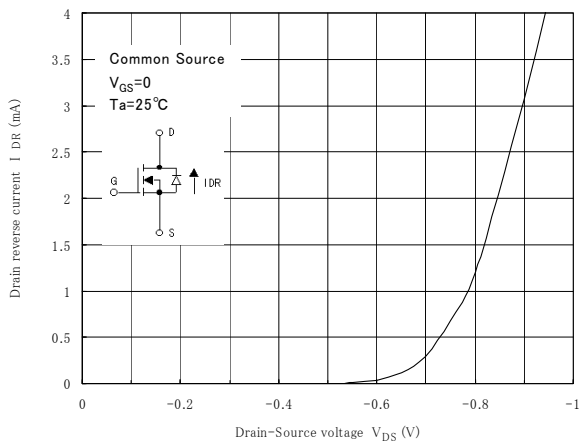
$|Y_{fs}| - I_D$ (MOSFET)



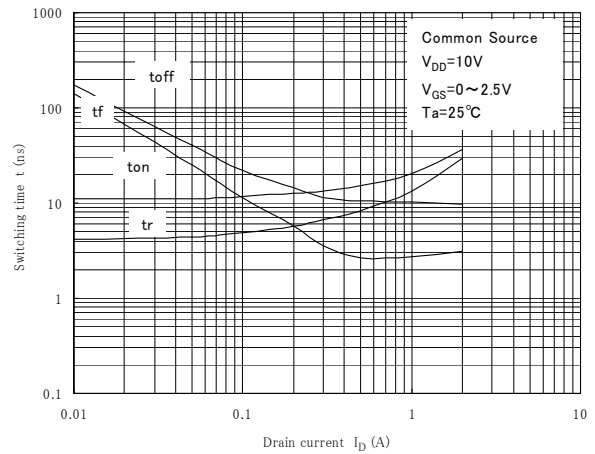
$C - V_{DS}$ (MOSFET)



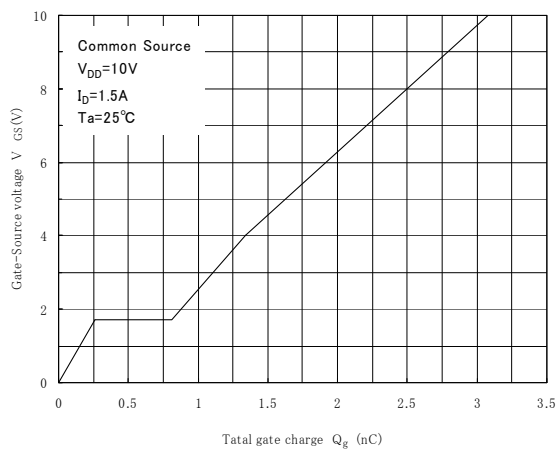
$I_{DR} - V_{DS}$ (MOSFET)



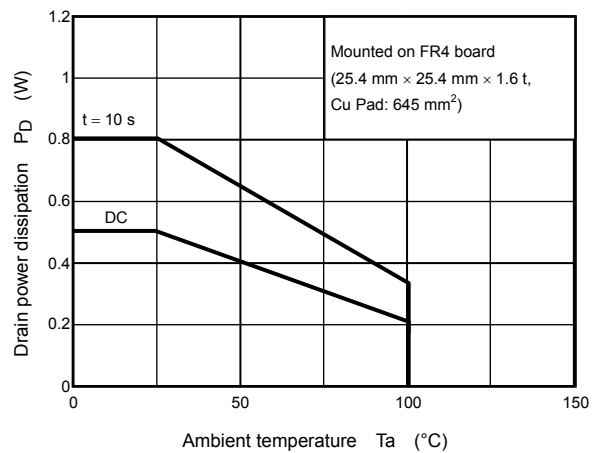
$t - I_D$ (MOSFET)

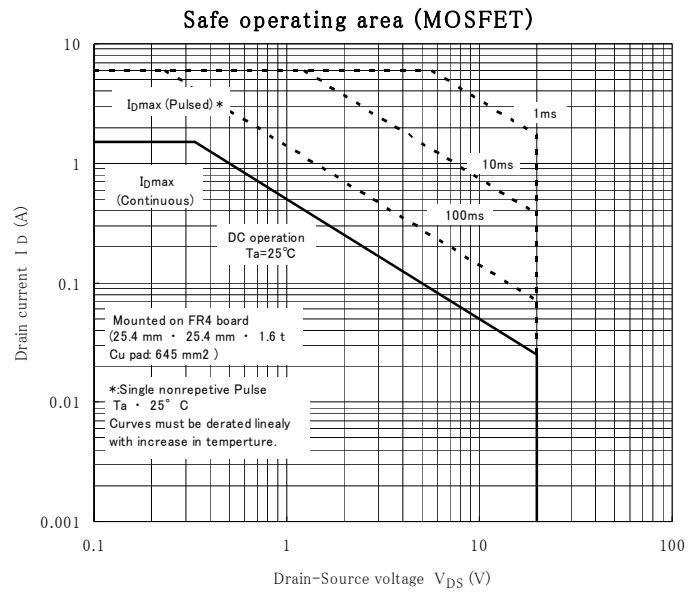


Dynamic Input Characteristic (MOSFET)

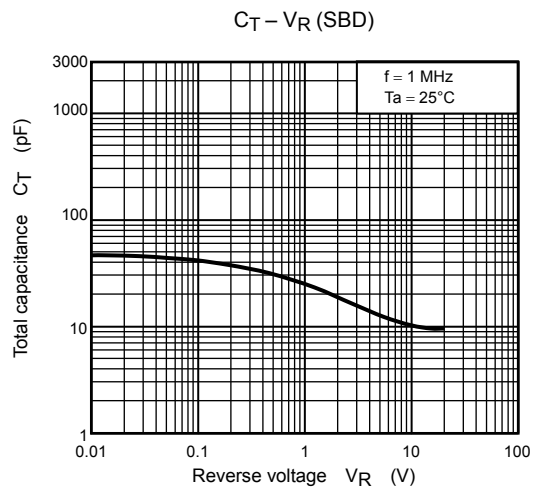
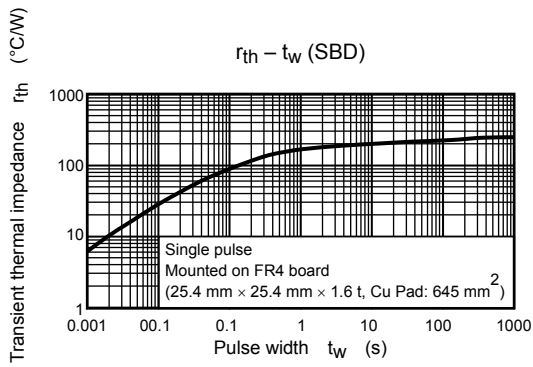
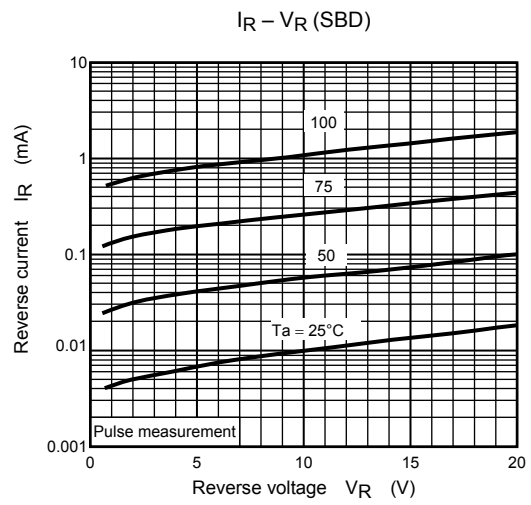
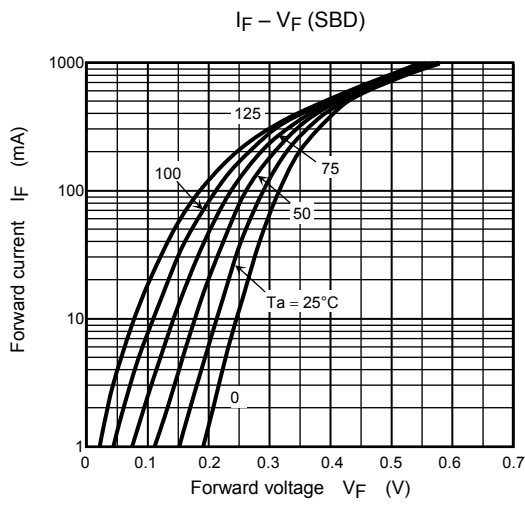


$P_D - T_a$ (MOSFET)

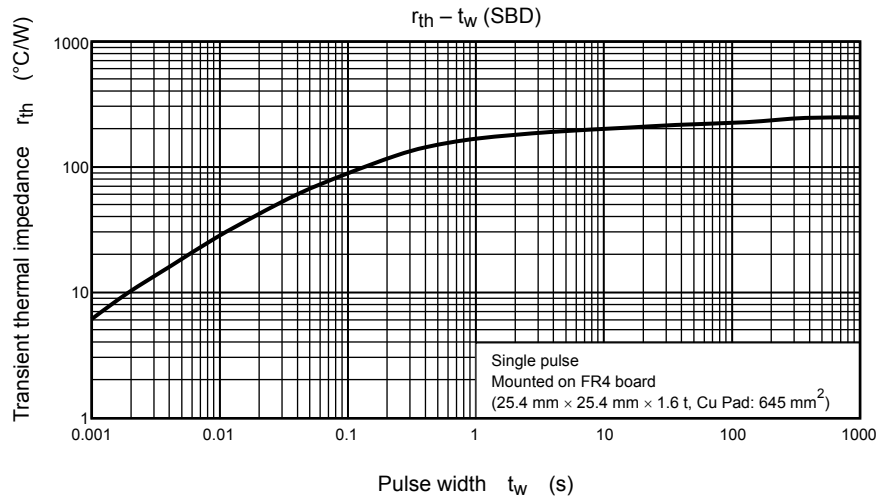
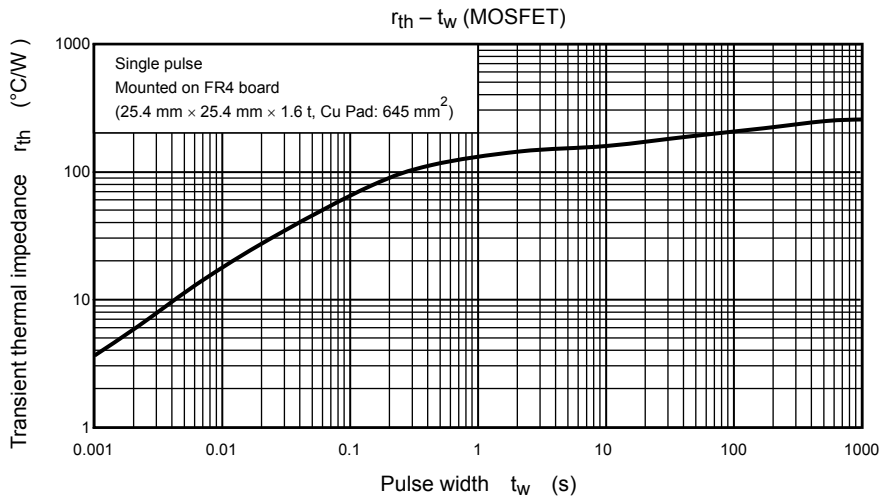




SBD Electrical Characteristics Graph



Transient Thermal Impedance Graph



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20070701-EN GENERAL

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